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OPTO ELECTRONICS
DETECTORS—PROGRAMMABLE UNIJUNCTION TRANSISTORS

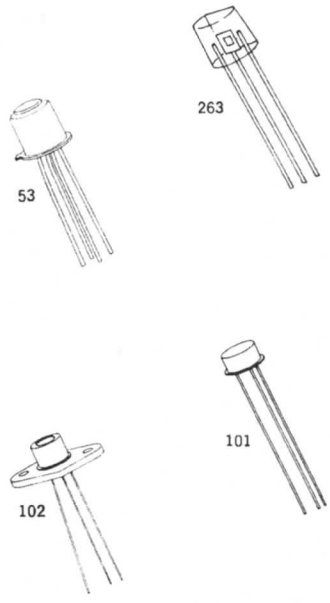
GE Type	Anode-Cathode Voltage Max. (V)	D.C. Anode Current Max. (mA)	RiseTime t_r Typical (nsec)	Irradiance to Trigger @ Rg=800KΩ, Vs=10V Max.	Forward on Voltage V_T Max. (V)	P_T Max. (mW)	Package Type	Package Outline No.	Specification Sheet No.
L14T	±40	100	80	1mW/Cm²	1.5	200	TO-92	263	55.54

OPTO ELECTRONICS
DETECTORS—SCSs

GE Type	Voltage Anode to Cathode Forward and Reverse Max. (V)	Forward Voltage at 175ma Anode Current @ R_{ge} = 27kΩ Max. (V)	Holding Current @ R_{ge} = 27kΩ Max. (mA)	Cathode Gate Current to Fire @ V_{AC} = 40V R_A = 800Ω Max. (μA)	Effective Irradiance To Trigger @ V_{AC} = 40V R_A = 800Ω Max.	Package Type	Package Outline No.	Specification Sheet No.
L1V	40	2.3	2.0	10	10mW/Cm²	TO-18	53	55.41

OPTO ELECTRONICS
DETECTORS—SCR's

GE Type	PRV/V_{BO}	I_{DC} @ 25°C Max. (A)	Max. Temp. °C Oper.	Max. Temp. °C Stor.	Effective Irradiance (mw/cm²) to Trigger [1] at 25°C T_J, 6Vdc Min.	Effective Irradiance (mw/cm²) to Trigger [1] at 25°C T_J, 6Vdc Max.	Package Outline No.	Specification Sheet No.
L8U	25	.44	100°	150°	0.68	10.0	101	190.10
L8F	50	.44	100°	150°	0.68	10.0	101	190.10
L8A	100	.44	100°	150°	0.68	10.0	101	190.10
L8B	150	.44	100°	150°	0.68	10.0	101	190.10
L8G	200	.44	100°	150°	0.68	10.0	101	190.10
L811U	25	.77	100°	150°	0.68	10.0	102	190.10
L811F	50	.77	100°	150°	0.68	10.0	102	190.10
L811A	100	.77	100°	150°	0.68	10.0	102	190.10
L811B	150	.77	100°	150°	0.68	10.0	102	190.10
L811G	200	.77	100°	150°	0.68	10.0	102	190.10
L9U	25	.44	100°	150°	0.68	4.2	101	190.10
L9F	50	.44	100°	150°	0.68	4.2	101	190.10
L9A	100	.44	100°	150°	0.68	4.2	101	190.10
L9B	150	.44	100°	150°	0.68	4.2	101	190.10
L9G	200	.44	100°	150°	0.68	4.2	101	190.10
L911U	25	.77	100°	150°	0.68	4.2	102	190.10
L911F	50	.77	100°	150°	0.68	4.2	102	190.10
L911A	100	.77	100°	150°	0.68	4.2	102	190.10
L911B	150	.77	100°	150°	0.68	4.2	102	190.10
L911G	200	.77	100°	150°	0.68	4.2	102	190.10



NOTE: Gate current to trigger from direct electrical supply is 20 μA typical, 200 μA maximum at 25°C T_J.

[1] Effective Irradiance to trigger decreases with increasing anode voltage and increasing gate to cathode resistance.

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors